

Silicon NPN Power Transistors

2N6259

DESCRIPTION

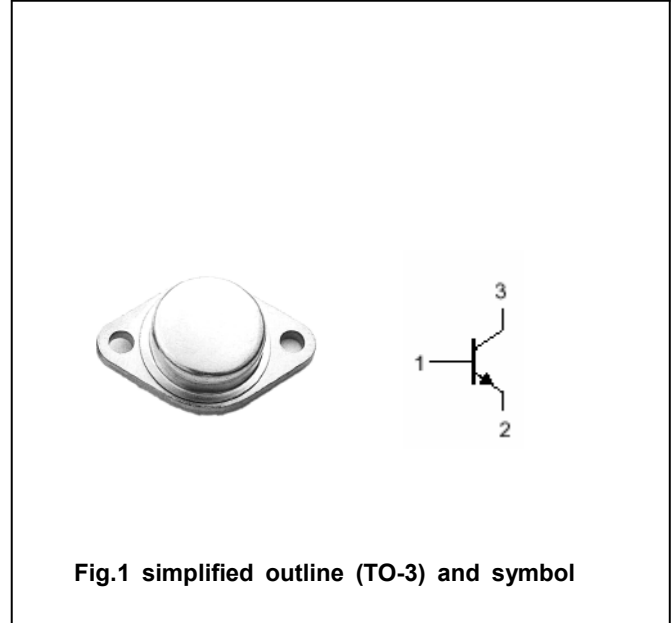
- With TO-3 package
- Low collector saturation voltage
- High power dissipation

APPLICATIONS

- Designed for high power audio ,disk head positioners,linear amplifiers,switching regulators solenoid drivers,and DC-DC converters or inverters

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	170	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		16	A
I_{CM}	Collector current-peak		30	A
I_B	Base current		4	A
I_{BM}	Base current-peak		15	A
P_D	Total Power Dissipation	$T_C = 25 \square$	150	W
T_j	Junction temperature		200	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.17	\square/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	150			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =8A ; I _B =0.8A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =16A ; I _B =3.2A			2.5	V
V _{BE}	Base-emitter on voltage	I _C =8A ; V _{CE} =2V			2.0	V
I _{CEO}	Collector cut-off current	V _{CE} =130V; I _B =0			10	mA
I _{CEx}	Collector cut-off current	V _{CE} =150V; V _{BE(off)} =1.5V			2.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			5.0	mA
h _{FE-1}	DC current gain	I _C =8A ; V _{CE} =2V	15		60	
h _{FE-2}	DC current gain	I _C =16A ; V _{CE} =4V	10			

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)